HAF2026RJ

Silicon N Channel Power MOS FET
Power Switching

REJ03G1255-0200
Rev.2.00
Jun 02, 2006

Description

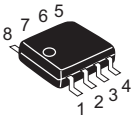
This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

Features

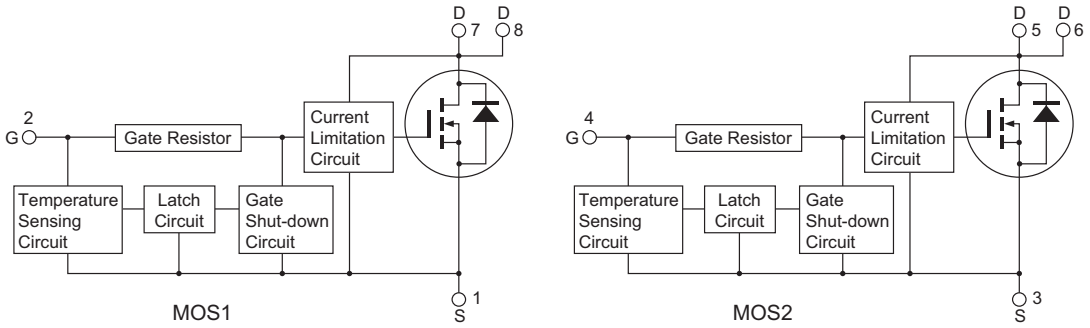
- Logic level operation (5 to 6 V Gate drive)
- Built-in the over temperature shut-down circuit
- High endurance capability against to the shut-down circuit
- Latch type shut down operation (need 0 voltage recovery)
- Built-in the current limitation circuit

Outline

RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8 (FP-8DAV))



1, 3	Source
2, 4	Gate
5, 6, 7, 8	Drain



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	16	V
Gate to source voltage	V_{GSS}	–2.5	V
Drain current	I_D	0.6	A
Body-drain diode reverse drain current	I_{DR}	1	A
Avalanche current	I_{AP} Note3	0.6	A
Avalanche energy	E_{AR} Note3	1.54	mJ
Cannel dissipation	Pch Note1	1	W
Cannel dissipation	Pch Note2	1.5	W
Cannel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. 1 Drive operation: When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s
2. 2 Drive operation: When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s
3. Tc = 25°C, Rg ≥ 50 Ω

Typical Operation Characteristics

(Ta=25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V_{IH}	3.5	—	—	V	
	V_{IL}	—	—	1.2	V	
Input current (Gate non shut down)	I_{IH1}	—	—	100	µA	Vi = 8 V, V_{DS} = 0
	I_{IH2}	—	—	50	µA	Vi = 3.5 V, V_{DS} = 0
	I_{IL}	—	—	1	µA	Vi = 1.2 V, V_{DS} = 0
Input current (Gate shut down)	$I_{IH(sd)1}$	—	0.53	—	mA	Vi = 8 V, V_{DS} = 0
	$I_{IH(sd)2}$	—	0.23	—	mA	Vi = 3.5 V, V_{DS} = 0
Shut down temperature	Tsd	—	175	—	°C	Cannel temperature
Gate operation voltage	Vop	3.5	—	12	V	
Drain current (Current limitation)	$I_{D\ limt}$	0.6	—	1.0	A	Vi = 5 V, V_{DS} = 3 V

Electrical Characteristics

(Ta = 25°C)

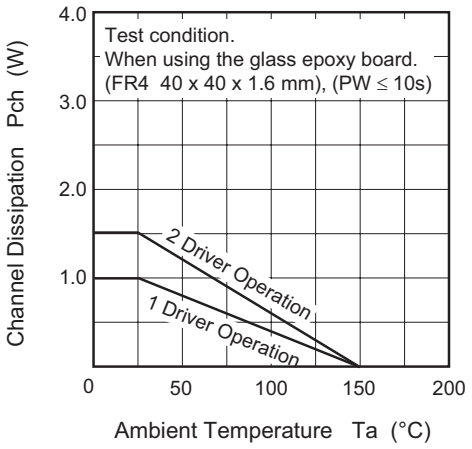
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I_{D1}	0.25	—	—	A	V_{GS} = 3.5 V, V_{DS} = 2 V
	I_{D2}	—	—	10	mA	V_{GS} = 1.2 V, V_{DS} = 2 V
	I_{D3}	0.6	—	1.0	A	V_{GS} = 5 V, V_{DS} = 3 V
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	16	—	—	V	I_G = 800 µA, V_{DS} = 0
	$V_{(BR)GSS}$	–2.5	—	—	V	I_G = –100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS1}	—	—	100	µA	V_{GS} = 8 V, V_{DS} = 0
	I_{GSS2}	—	—	50	µA	V_{GS} = 3.5 V, V_{DS} = 0
	I_{GSS3}	—	—	1	µA	V_{GS} = 1.2 V, V_{DS} = 0
	I_{GSS4}	—	—	–100	µA	V_{GS} = –2.4 V, V_{DS} = 0
Input current (shut down)	$I_{GS(OP)1}$	—	0.53	—	mA	V_{GS} = 8 V, V_{DS} = 0
	$I_{GS(OP)2}$	—	0.23	—	mA	V_{GS} = 3.5 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS1}	—	—	10	µA	V_{DS} = 60 V, V_{GS} = 0
	I_{DSS2}	—	—	10	µA	V_{DS} = 48 V, V_{GS} = 0, Ta = 125°C
Gate to source cut off voltage	$V_{GS(off)}$	1.4	—	2.5	V	V_{DS} = 10 V, I_D = 1 mA
Forward transfer admittance	$\|y_{fs}\|$	0.26	1.3	—	S	I_D = 0.5 A, V_{DS} = 10 V[Note4]
Static drain to source on state resistance	$R_{DS(on)}$	—	200	300	mΩ	I_D = 0.5 A, V_{GS} = 5 V[Note4]
	$R_{DS(on)}$	—	150	210	mΩ	I_D = 0.5 A, V_{GS} = 10 V[Note4]
Output capacitance	Coss	—	140	—	pF	V_{DS} = 10 V, V_{GS} = 0, f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	2.9	—	µs	V_{GS} = 5 V, I_D= 0.5 A, R_L = 60 Ω
Rise time	t_r	—	11	—	µs	
Turn off delay time	$t_{d(off)}$	—	0.9	—	µs	
Fall time	t_f	—	1	—	µs	
Body-drain diode forward voltage	V_{DF}	—	0.9	—	V	I_F = 1 A, V_{GS} = 0
Body-drain diode reverse recovery time	t_{rr}	—	61	—	ns	I_F = 1 A, V_{GS} = 0, di_F/dt = 50 A/µs
Over load shut down operation time [note5]	t_{os1}	—	85	—	ms	V_{GS} = 5 V, V_{DD} = 16 V
	t_{os2}	—	30	—	ms	V_{GS} = 5 V, V_{DD} = 24 V

Notes: 4. Pulse test

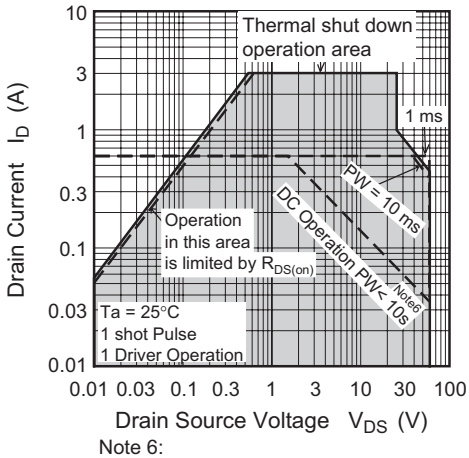
5. Including the junction temperature rise of the over lorded condition.

Main Characteristics

Power vs. Temperature Derating

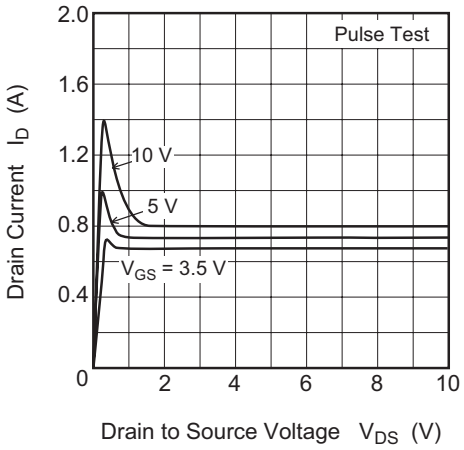


Maximum Safe Operation Area

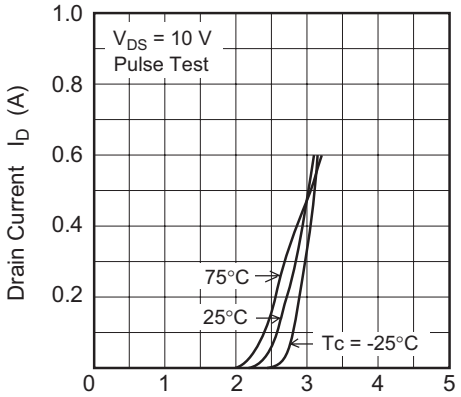


Note 6:
When using the glass epoxy board.
(FR4 40 x 40 x 1.6 mm)

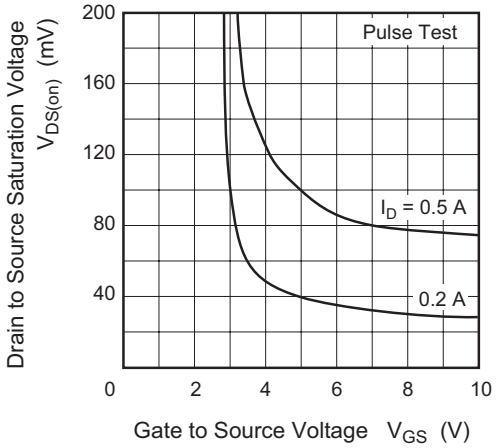
Typical Output Characteristics



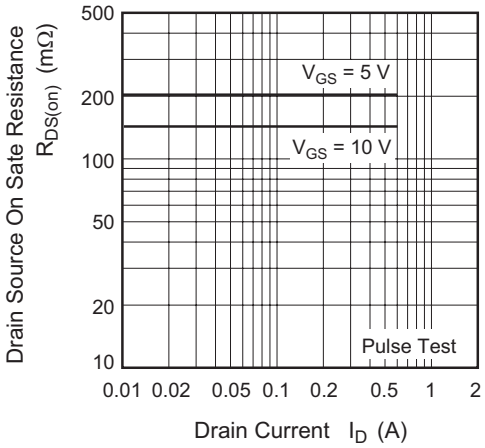
Typical Transfer Characteristics



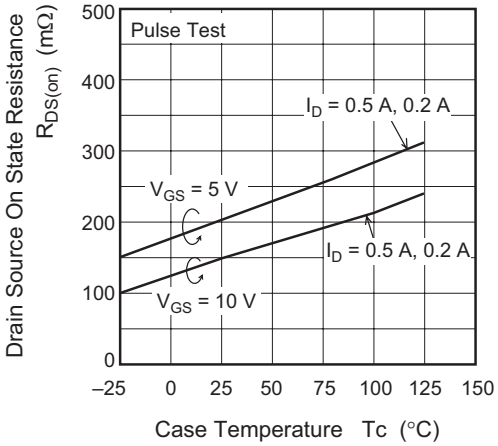
Drain to Saturation Voltage vs. Gate to Source Voltage



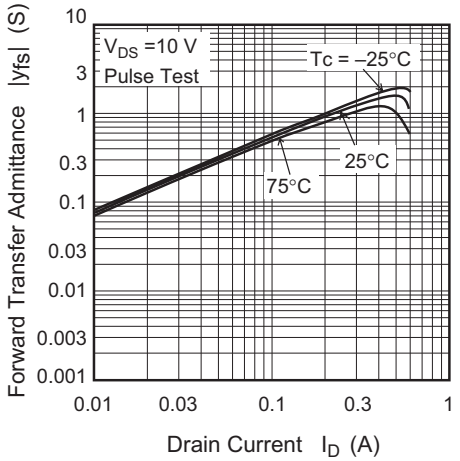
Static Drain to Source State Resistance vs. Drain Current



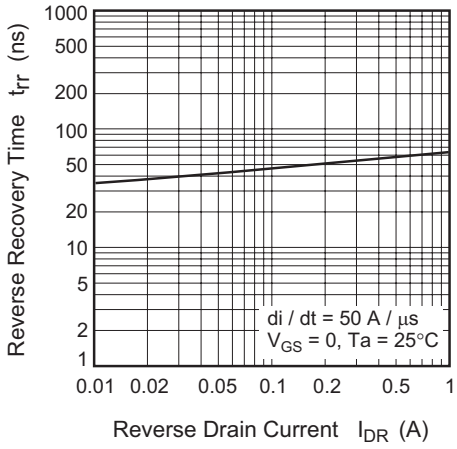
Drain to Source On State Resistance vs. Temperature



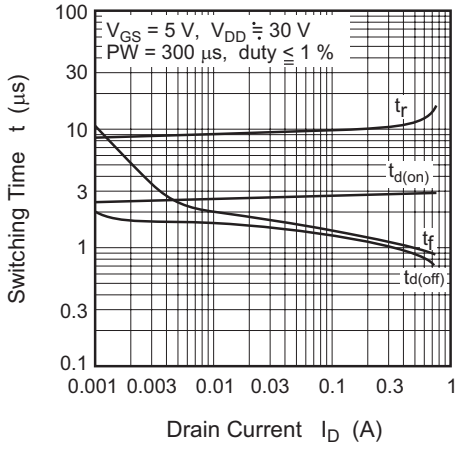
Forward Transfer Admittance vs. Drain Current



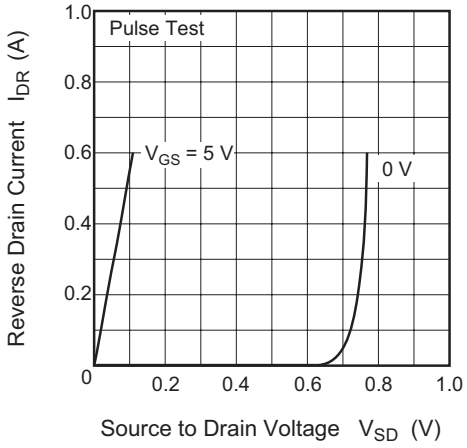
Body to Drain Diode Reverse Recovery Time



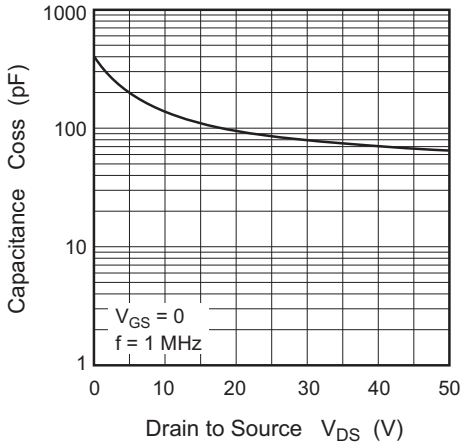
Switching Characteristics



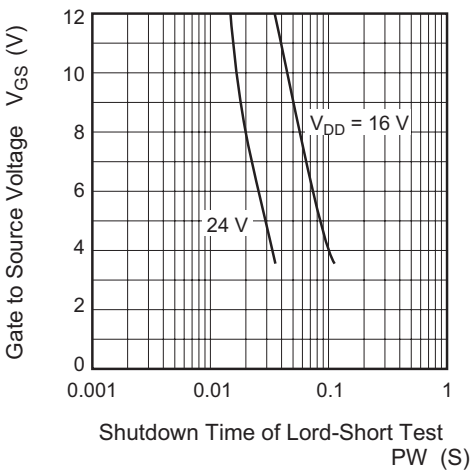
Reverse Drain Current vs. Source to Drain Voltage



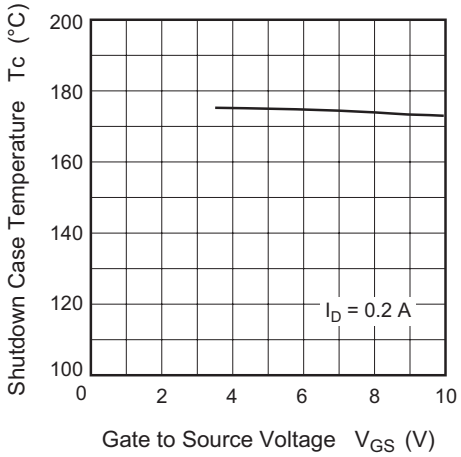
Typical capacitance vs. Drain to Source Voltage



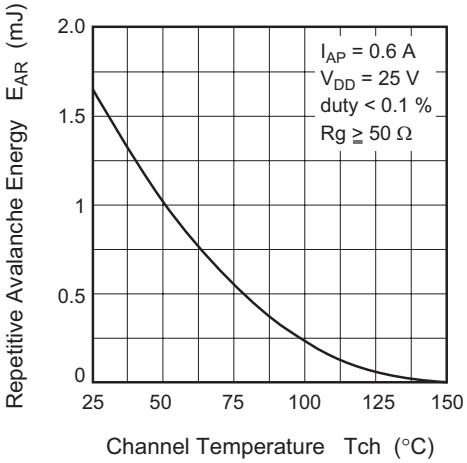
Gate to Source Voltage vs.
Shutdown Time of Load-Short Test



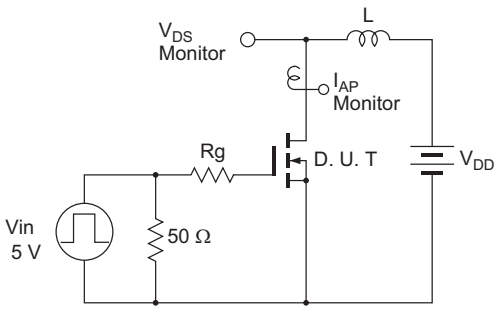
Shutdown Case Temperature vs.
Gate to Source Voltage



Avalanche Energy vs.
Channel Temperature Derating

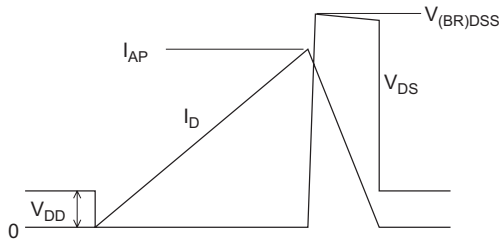


Avalanche Test Circuit

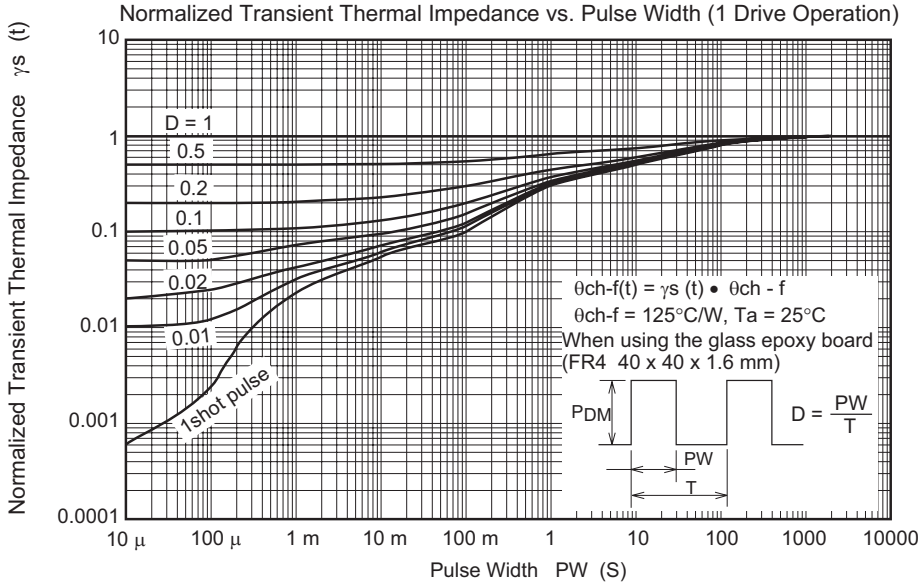


Avalanche Waveform

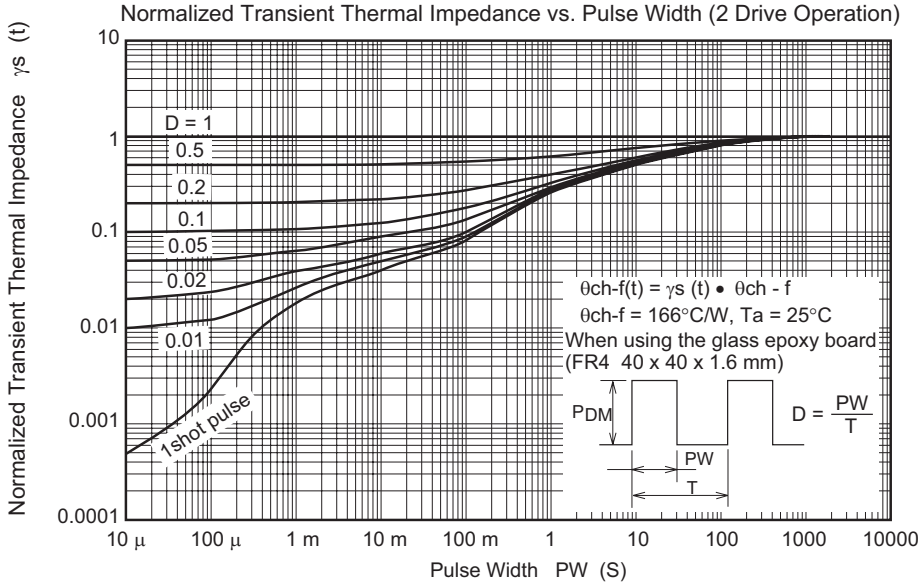
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



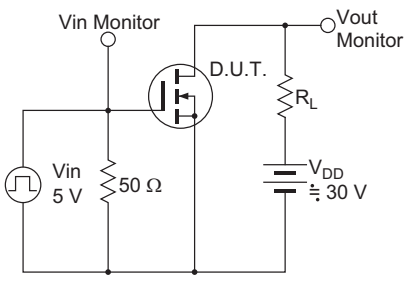
Normalized Transient Thermal Impedance vs. Pulse Width (1 Drive Operation)



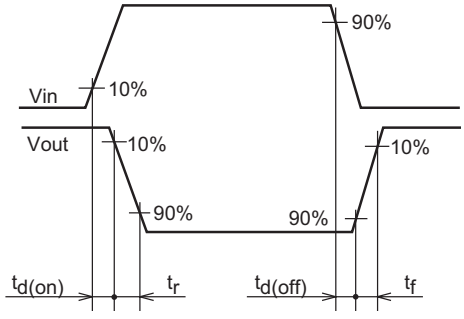
Normalized Transient Thermal Impedance vs. Pulse Width (2 Drive Operation)



Switching Time Test Circuit

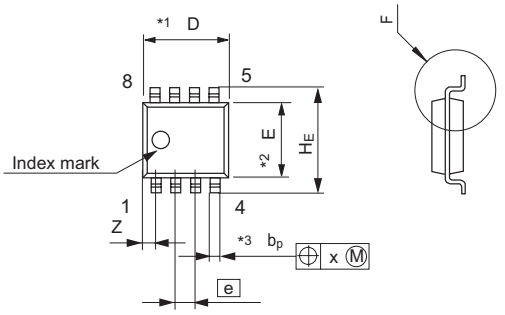


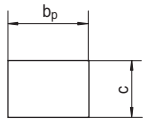
Switching Time Waveform



Package Dimensions

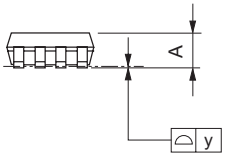
Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
SOP-8	P-SOP8-3.95 × 4.9-1.27	PRSP0008DD-D	FP-8DAV	0.085g

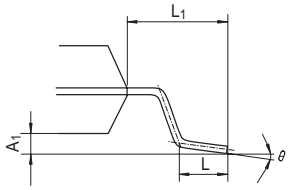




Terminal cross section
(Ni/Pd/Au plating)

NOTE)
1. DIMENSIONS "*1(Nom)" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.





Detail F

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	4.90	5.3
E	—	3.95	—
A_2	—	—	—
A_1	0.10	0.14	0.25
A	—	—	1.75
b_p	0.34	0.40	0.46
b_1	—	—	—
c	0.15	0.20	0.25
c_1	—	—	—
θ	0°	—	8°
H_E	5.80	6.10	6.20
e	—	1.27	—
x	—	—	0.25
y	—	—	0.1
Z	—	—	0.75
L	0.40	0.60	1.27
L_1	—	1.08	—

Ordering Information

Part Name	Quantity	Shipping Container
HAF2026RJ-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated.
Please contact the Renesas sales office to check the state of production before ordering the product.

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http://www.renesas.com

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Colophon .6.0